

<b>SANYO</b>	No.4221	<b>2SJ285</b>
		P-Channel MOS Silicon FET Very High-Speed Switching Applications

**Features**

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.

**Absolute Maximum Ratings at Ta = 25°C**

			unit
Drain to Source Voltage	V <sub>DSS</sub>	-60	V
Gate to Source Voltage	V <sub>GSS</sub>	±15	V
Drain Current(DC)	I <sub>D</sub>	-250	mA
Drain Current(Pulse)	I <sub>DP</sub>	-1	A
Allowable Power Dissipation	P <sub>D</sub>	250	mW
Channel Temperature	T <sub>ch</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

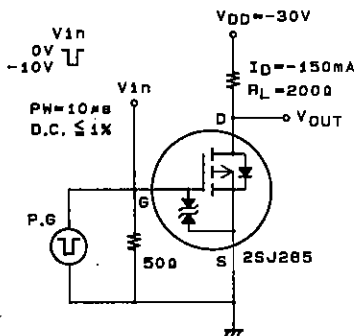
PW ≤ 10μs, duty cycle ≤ 1%

**Electrical Characteristics at Ta = 25°C**

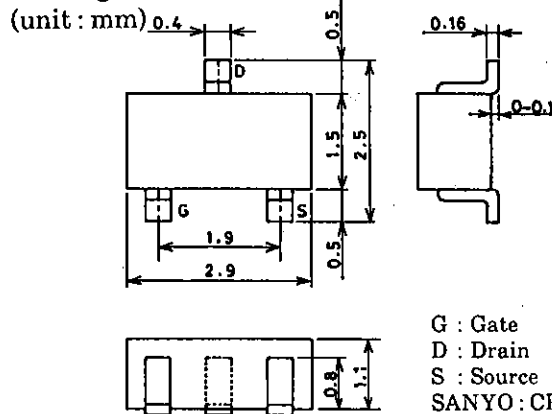
			min	typ	max	unit
D-S Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = -1mA, V <sub>GS</sub> = 0	-60			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -60V, V <sub>GS</sub> = 0			-100	μA
Gate to Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = -10V, I <sub>D</sub> = -1mA	-1.0		-2.0	V
Forward Transfer Admittance	Y <sub>fs</sub>	V <sub>DS</sub> = -10V, I <sub>D</sub> = -150mA	200	350		mS
Static Drain to Source on State Resistance	R <sub>DS(on)</sub>	I <sub>D</sub> = -150mA, V <sub>GS</sub> = -10V		2.2	3.0	Ω
	R <sub>DS(on)</sub>	I <sub>D</sub> = -150mA, V <sub>GS</sub> = -4V		3.0	4.0	Ω
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -20V, f = 1MHz		45		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = -20V, f = 1MHz		20		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> = -20V, f = 1MHz		5		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit.		7		ns
Rise Time	t <sub>r</sub>	"		10		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>	"		40		ns
Fall Time	t <sub>f</sub>	"		35		ns
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = -250mA, V <sub>GS</sub> = 0		-1		V

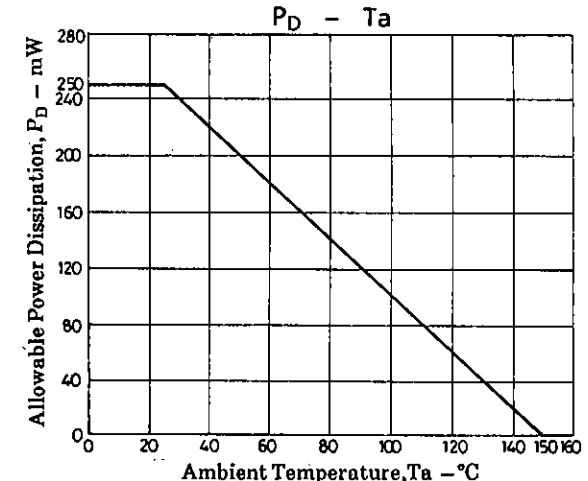
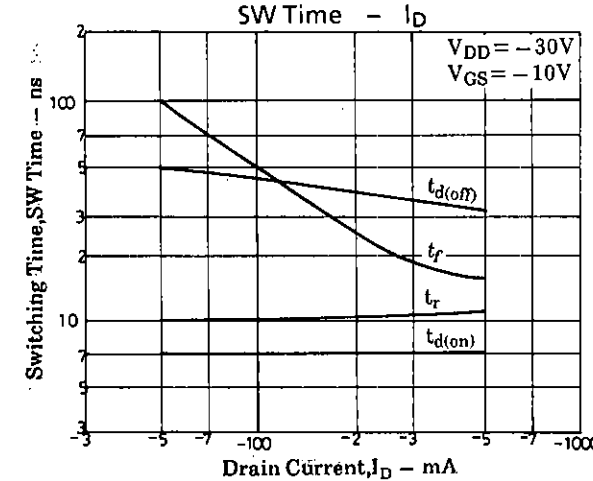
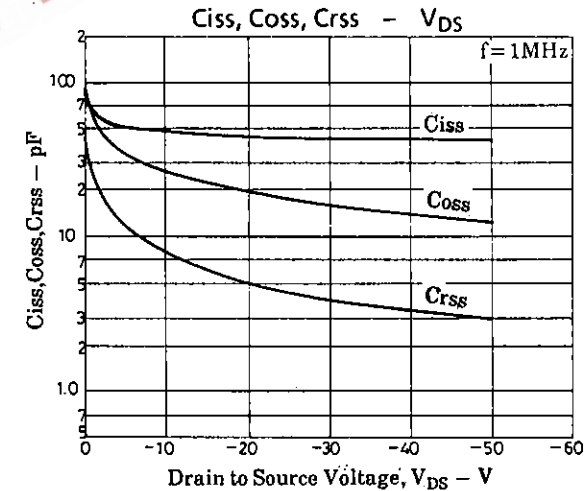
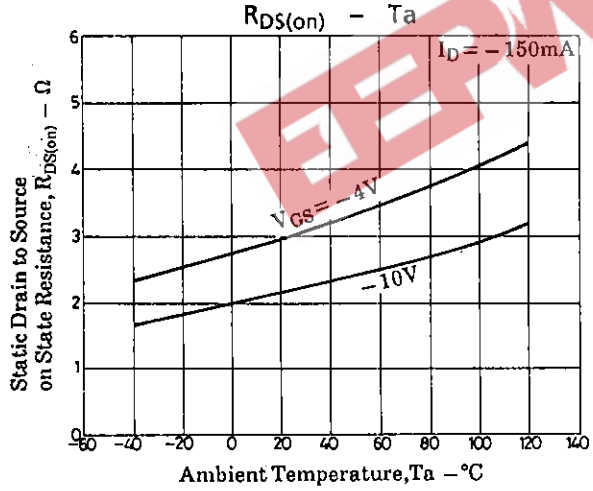
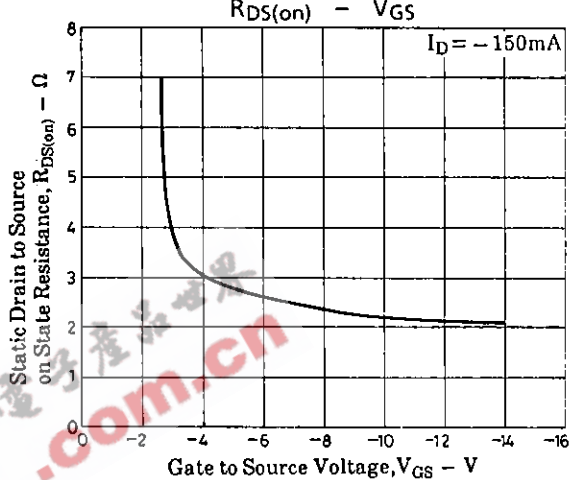
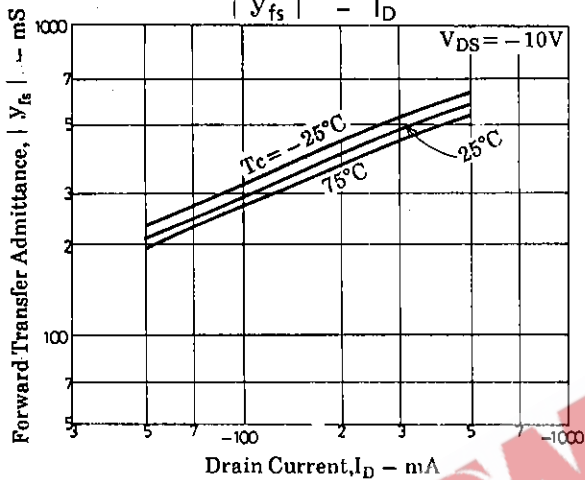
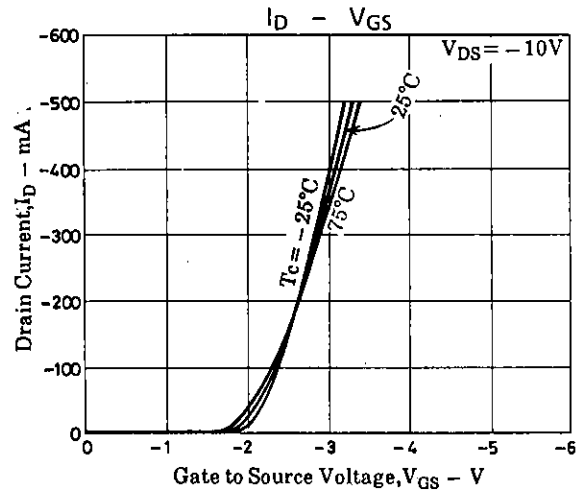
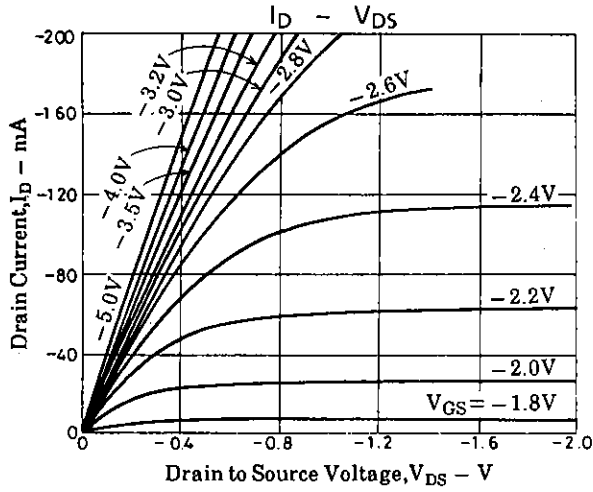
Marking : BM

**Switching Time Test Circuit**



**Package Dimensions 2091**





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